



#7/A  
4/8/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

: Conf. No.:

Maria Ronay

Serial No.: 09/577,347

: Art Unit: 1765

Filed: May 24, 2000

: Examiner: Perez Ramos, V.

For: Selective Polishing with  
Slurries Containing  
Polyelectrolytes

: Atty Docket: 20140/0247

RECEIVED  
APR 05 2002  
TC 1700

**RESPONSE AND AMENDMENT UNDER 37 CFR § 1.111**

Commissioner for Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action dated January 3, 2002, please amend the above-captioned application as follows:

**IN THE CLAIMS:**

Please cancel claims 2-12 without prejudice or disclaimer to their reentry at a later date and amend claims 13 and 18 as follows:

13. (Amended) A method for polishing a silicon dioxide surface in contact with a silicon nitride which comprises providing on the silicon dioxide surface a slurry comprising abrasive particles and an anionic polyelectrolyte in an amount sufficient to increase the polishing rate ratio of the silicon dioxide to the silicon nitride and contact said surface with a polishing pad.